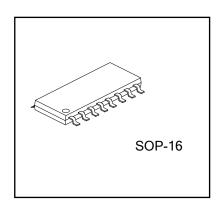


# 3.0V TO 5.5V LOW POWER MULTICHANNEL RS-232 LINE TRANSCEIVERS USING FOR 0.1 µF EXTERNAL CAPACITORS



#### **DESCRIPTION**

The ST3232BDR has two receivers and two drivers, and a dual charge-pump circuit. The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3.0V to 5.5V supply. The device operates at data signaling rates up to 250kbit/s and a maximum of  $35V/\mu s$  driver output slew rate.

#### **FEATURES**

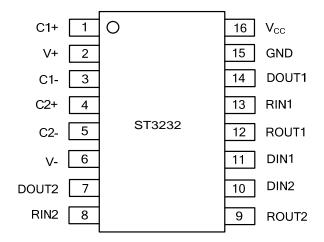
- \* Exceeds ±8KV ESD Protection(HBM) for RS-232 I/O Pins
- \* Meets the Requirements of TIA/EIA-232-F and ITU V.28 Standards
- \* Operates With 3.0V to 5.5V V<sub>CC</sub> Supply
- \* Operates Up To 250kbit/s Data Rate
- \* Two Drivers and Two Receivers
- \* External Capacitors 4×0.1µF
- \* Accepts 5.0V Logic Input With 3.3V Supply

Rev:2023A2

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#### **PIN CONFIGURATION**



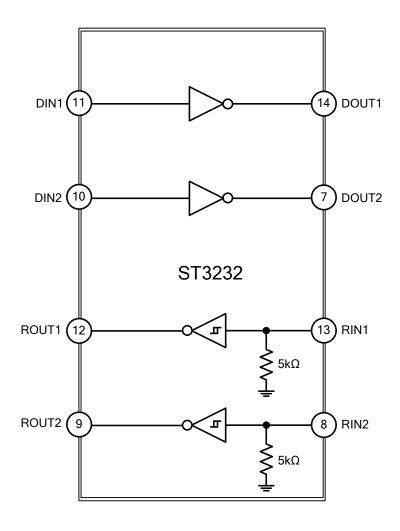
#### **PIN DESCRIPTION**

PIN NO.	PIN NAME	DESCRIPTION
1	C1+	Positive Terminal of Voltage-Doubler Charge-Pump Capacitor
2	V+	+5.5V Generated by the Charge Pump
3	C1-	Negative Terminal of Voltage-Doubler Charge-Pump Capacitor
4	C2+	Positive Terminal of Inverting Charge-Pump Capacitor
5	C2-	Negative Terminal of Inverting Charge-Pump Capacitor
6	V-	-5.5V Generated by the Charge Pump
7	DOUT2	RS-232 Driver Outputs
8	RIN2	RS-232 Receiver Inputs
9	ROUT2	TTL/CMOS Receiver Outputs
10	DIN2	TTL/CMOS Driver Inputs
11	DIN1	TTL/CMOS Driver Inputs
12	ROUT1	TTL/CMOS Receiver Outputs
13	RIN1	RS-232 Receiver Inputs
14	DOUT1	RS-232 Driver Outputs
15	GND	Ground
16	$V_{CC}$	+3.0V to +5.5V Supply Voltage

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#### **BLOCK DIAGRAM**



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#### ABSOLUTE MAXIMUM RATING [Over operating free-air temperature range (unless otherwise noted)]

PARAMETER		SYMBOL	RATINGS	UNIT
Supply Voltage Range		$V_{CC}$	-0.3 ~ +6.0	V
Positive Output Supply Voltage Ran	ige (Note 2)	V+	-0.3 ~ +7.0	V
Negative Output Supply Voltage Ra	nge (Note 2)	V-	+0.3 ~ -7.0	V
Supply Voltage Difference (Note 2)		V+ - V-	+13	V
lancit Valtage	Drivers		-0.3 ~ +6.0	V
Input Voltage	Receivers	$V_{IN}$	-25 ~ +25	V
Output Valtage	Drivers	M	-13.2 ~ +13.2	V
Output Voltage	Receivers	$V_{OUT}$	-0.3 ~ V <sub>CC</sub> +0.3	V
Operating Virtual Junction Temperature		TJ	+150	°C
Storage Temperature		T <sub>STG</sub>	-65 ~ + 150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	SOP-16	θја	105	°C/W

# RECOMMENDED OPERATING CONDITIONS (See Note & Table 1)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Supply Voltage	V	V <sub>CC</sub> =3.3V		3.0	3.3	3.6	V
Supply Voltage	V <sub>CC</sub>	V <sub>CC</sub> =5.0V		4.5	5.0	5.5	V
Driver and Control High-level Input	\/	DIN	$V_{CC}$ =3.3 $V$	2.0			\/
Voltage	$V_{IH}$	DIIN	V <sub>CC</sub> =5.5V	2.4			V
Driver and Control Low-level Input Voltage	$V_{IL}$	DIN				0.8	V
Driver and Control Input Voltage	$V_{IN}$	DIN				5.5	V
Receiver Input Voltage	$V_{RIN}$			-25		25	V
Operating Free-Air Temperature	T <sub>A</sub>			0		70	°C

Notes: Test conditions are C1~C4=0.1 $\mu$ F at V<sub>CC</sub>=3.3V±0.3V; C1=0.047 $\mu$ F, C2~C4=0.33 $\mu$ F at V<sub>CC</sub>=5.0V±0.5V.

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<sup>2.</sup> All voltages are with respect to network GND.



**ELECTRICAL CHARACTERISTICS** [(over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 3 & Table 1)]

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP (Note 1)	MAX	UNIT
Supply Current	I <sub>CC</sub>	No load		0.3	1.0	mA
DRIVER SECTION						
High-Level Output Voltage	$V_{OH}$	DOUT at R <sub>L</sub> =3kΩ to GND, DIN=GND	+5.0	+5.4		V
Low-Level Output Voltage	$V_{OL}$	DOUT at $R_L$ =3k $\Omega$ to GND, DIN= $V_{CC}$	-5.0	-5.4		V
High-Level Input Current	I <sub>OH</sub>	$V_I = V_{CC}$		±0.01	±1	μΑ
Low-Level Input Current	$I_{OL}$	V₁ at GND		±0.01	±1	μΑ
Short-Circuit Output Current		$V_{CC}$ =3.6V, $V_{OUT}$ =0V		±35	±60	mA
(Note 2)	los	V <sub>CC</sub> =5.5V, V <sub>OUT</sub> =0V		±35	±60	mA
Output Resistance	$r_{O}$	V <sub>CC</sub> , V+ and V- =0V, V <sub>OUT</sub> =±2.0V	300	10M		Ω
RECEIVER SECTION						
High-Level Output Voltage	$V_{OH}$	I <sub>OH</sub> =-1.0mA	V <sub>CC</sub> -0.6V	V <sub>CC</sub> - 0.1V		V
Low-Level Output Voltage	$V_{OL}$	I <sub>OL</sub> =1.6mA			0.4	V
Positive-Going Input Threshold	\/	V <sub>CC</sub> =3.3V		1.5	2.4	V
Voltage	$V_{IT+}$	V <sub>CC</sub> =5.0V		1.8	2.4	V
Negative-Going Input	\/	V <sub>CC</sub> =3.3V	0.6	1.2		V
Threshold Voltage	$V_{IT}$	V <sub>CC</sub> =5.0V	0.8	1.5		V
Input Hysteresis	$V_{HYS}$	$V_{IT+} \sim V_{IT-}$		0.3		V
Input Resistance	Rı	V <sub>I</sub> =±3.0V~±25V	3	5	7	kΩ

Notes: 1. All typical values are at  $V_{CC}$ =3.3V or  $V_{CC}$ =5.0V, and  $T_A$ =25°C.

- 2. Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.
- 3. Test conditions are C1~C4=0.1 $\mu$ F at V<sub>CC</sub>=3.3V±0.3V; C1=0.047 $\mu$ F, C2~C4=0.33 $\mu$ F at V<sub>CC</sub>=5.0V±0.5V.
- 4. Pulse skew is defined as |t<sub>PLH</sub>-t<sub>PHL</sub>| of each channel of the same device.

**SWITCHING CHARACTERISTICS** [over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 3 and Table 1)]

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP (Note 1)	MAX	UNIT
DRIVER SECTION							_
Maximum Data Rate		$C_L$ =1000pF, $R_L$ =3k $\Omega$ , One Driver Switching		120		250	Kbit/s
Pulse Skew (Note 4)	t <sub>SK(p)</sub>	C <sub>L</sub> =220pF~250	0pF, R <sub>L</sub> =3kΩ~7kΩ		300		ns
Slew Rate, Transition Region	SR(tr)	$R_L = 3k\Omega \sim 7k\Omega$ ,	C <sub>L</sub> =220pF~1000pF	5		35	V/us
Siew Rate, Transition Region		V <sub>CC</sub> =3.3V	C <sub>L</sub> =220pF~2500pF	3		35	V/µs
RECEIVER SECTION							
Propagation Delay Time, Low-to High-Level Output	t <sub>PLH</sub>	C <sub>L</sub> =150pF			300		ns
Propagation Delay Time, Highto Low-Level Output	t <sub>PHL</sub>	C <sub>L</sub> =150pF			300		ns
Output Enable Time	t <sub>EN</sub>	$C_L=150pF, R_L=3k\Omega$			200		ns
Output Disable Time	t <sub>DIS</sub>	$C_L=150pF, R_L=3k\Omega$			200		ns
Pulse Skew (Note 4)	t <sub>SK(P)</sub>	t <sub>PLH</sub> -t <sub>PHL</sub>			300		ns

Notes: 1. All typical values are at  $V_{CC}$ =3.3V or  $V_{CC}$ =5.0V, and  $T_A$ =25°C.

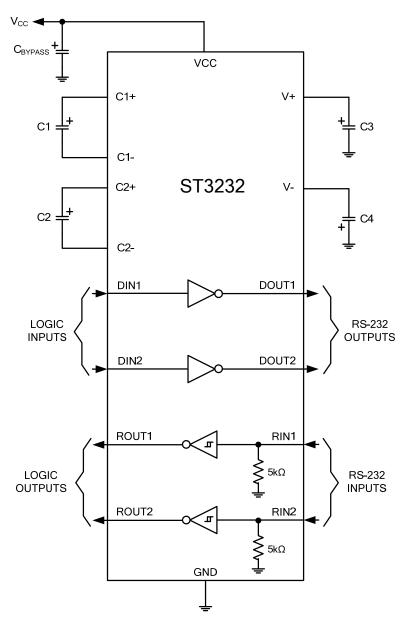
- 2. Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.
- 3. Test conditions are C1~C4=0.1µF at V<sub>CC</sub>=3.3V±0.3V; C1=0.047µF, C2~C4=0.33µF at V<sub>CC</sub>=5.0V±0.5V.

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4. Pulse skew is defined as |tplh-tphl| of each channel of the same device.



#### **TYPICAL APPLICATION CIRCUIT**



- Notes: 1. C3 can be connected to V<sub>CC</sub> or GND.
  2. Resistor values shown are nominal.
  3. NC: No internal connection.

  - 4. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

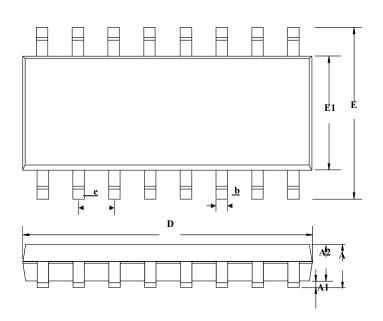
Table 1. Typical Operating Circuit and Capacitor Values

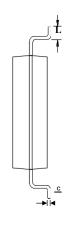
V <sub>CC</sub> (V)	C1 (µF)	C2, C3, C4 (µF)	C <sub>BYPASS</sub> (µF)
3.0~3.6	0.22	0.22	0.22
3.15~3.6	0.1	0.1	0.1
4.5~5.5	0.047	0.33	0.047
3.0~5.5	0.22	1.0	0.22



### PACKAGE: SOP-16

UNIT: mm





SYMBOL	MILLIMETER				
3 I MIBOL	MIN NOM		MAX		
A	_	_	1.80		
A1	0.10	0.15	0.25		
A2	1.25	1.45	1.65		
b	0.33	_	0.51		
с	0.17	_	0.25		
D	9.50	_	10.20		
Е	5.80	6.00	6.20		
E1	3.70		4.10		
e	1.27BSC				
L	0.45	0.60	0.80		

## **ORDERING INFORMATION**

Ordering Number	Package	Baseqty	Packing
ST3232BDR	SOP-16	2500	Tape and reel